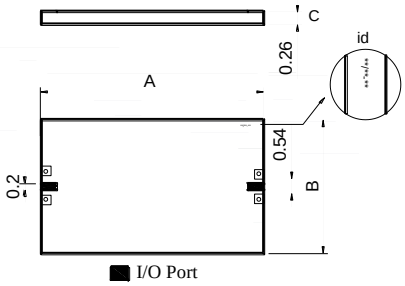
EC MICROWAVE
The door to the RF world

Thin Film ceramic Filte

BMBP30R7/3R8-6PA



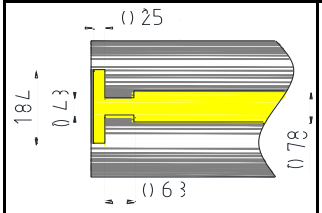
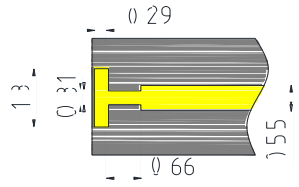
Precautions

1. The chip is recommended sub-cavity use, both sides of the side wall from about 0.2mm, surface distance Cover about 3mm, the chip ports are interchangeable;

2. Chip recommended low-stress conductive adhesive (such as ME8456) bonding;

3. Chip should be installed in Kovar (recommended) or molybdenum copper with ceramic thermal expansion coefficient(6.7ppm / ℃) on the carrier, the carrier thickness ≥ 0.2mm;

4 circuit board micro-chip wire bonding connection, it is recommended microstrip bonding at mining T-type structure to match, T-size as right

Circuit boardRogers 5880，10mil	Circuit boardRogers 4350，10mi l
	
frequency: DC-38GHz	frequency: DC-32GHz

注：T 型图形顶端基板白边 50um；频率 10GHz 以下无需匹配

Features

high-precision film processing technology
high performance, low temperature drift, high power
Ceramic substrate, 50Ω coplanar waveguide output
Gold wire bonding, suitable for multi-chip integrated module applications

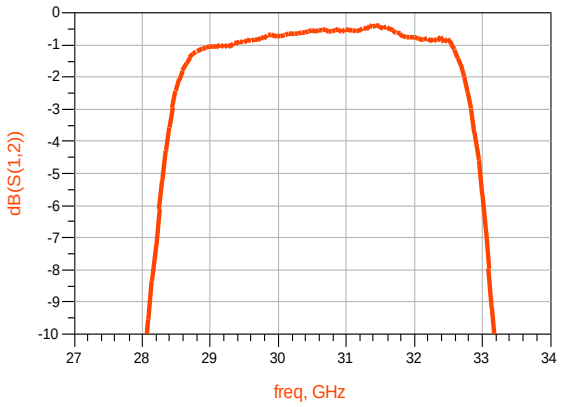
Environmental parameters

Working temperature	-55℃~+85℃
storage temperature	-55℃~+125℃
Maximum input power	35dBm

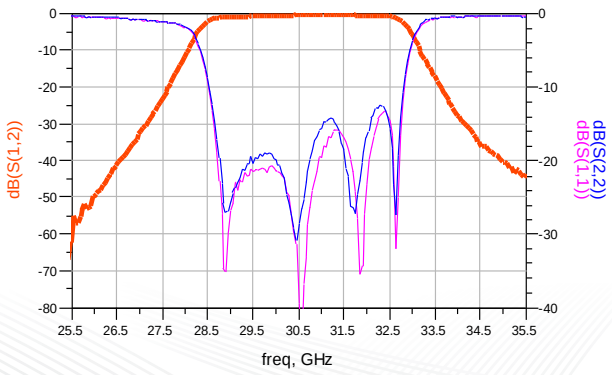
Electrical Specifications

Center frequency(f0)	30.7
Passband frequency range (GHz)	28.8-32.6
Band fluctuations (dB)	1
Center insertion loss (dB)	2.0
Return loss (dB)	10
Band attenuation (dB)	≥ 40@26.4GHz ≥ 40@35.2GHz

Passband loss VS frequency (T_A=25℃)



Band rejection & Return loss VS frequency (T_A=25℃)



Distal inhibition VS frequency (T_A=25℃)